

Applicant: Lih-Ping Li  
Serial No.: 10/810,912  
Attorney Docket No.: 67,200-1256

---

**IN THE CLAIMS**

Please amend claims 1, 5, 6 and 10-13 as follows.

1. (Currently amended) A method of seasoning a process chamber having interior surfaces, comprising the steps of:

cleaning said process chamber; and

providing a seasoning film having a thickness of from about 2  $\mu$ m to about 10  $\mu$ m on said interior surfaces of said process chamber by introducing precursor gases into said process chamber at a chamber pressure of from about 10 Torr to about 760 Torr.

2. (Original) The method of claim 1 wherein said seasoning film comprises oxide-based material.

3. (Original) The method of claim 1 wherein said seasoning film comprises silicon nitride.

4. (Original) The method of claim 1 wherein said seasoning film comprises silicon carbide.

Applicant: Lih-Ping Li  
Serial No.: 10/810,912  
Attorney Docket No.: 67,200-1256

---

5. (Currently amended) A method of seasoning a chemical vapor deposition chamber having interior surfaces and a gas distribution plate, comprising the steps of:

cleaning said chamber; and

providing a seasoning film having a thickness of from about 2  $\mu\text{m}$  to about 10  $\mu\text{m}$  on said interior surfaces and said gas distribution plate of said chamber by introducing precursor gases into said process chamber at a chamber pressure of from about 10 Torr to about 760 Torr at a temperature of from about 500 degrees C to about 700 degrees C.

6. (Currently amended) The method of claim 5 wherein said seasoning film comprises ~~silicon dioxide~~ oxide-based material.

7. (Original) The method of claim 5 wherein said seasoning film comprises silicon dioxide.

8. (Original) The method of claim 5 wherein said seasoning film comprises silicon nitride.

9. (Original) The method of claim 5 wherein said seasoning film comprises silicon carbide.

Applicant: Lih-Ping Li  
Serial No.: 10/810,912  
Attorney Docket No.: 67,200-1256

---

10. (Currently amended) A method of seasoning a chemical vapor deposition chamber having interior surfaces and a gas distribution plate, comprising the steps of:

cleaning said chamber; and

providing a seasoning film having a thickness of from about 2  $\mu\text{m}$  to about 10  $\mu\text{m}$  on said interior surfaces and said gas distribution plate of said chamber by introducing seasoning film precursor gases into said chamber at a chamber pressure of from about 10 Torr to about 760 Torr at a temperature of from about 500 degrees C to about 700 degrees C and a process time of from about 0.5 minutes to about 10 minutes.

11. (Currently amended) The method of claim ~~17~~ 10 wherein said seasoning film comprises silicon dioxide.

12. (Currently amended) The method of claim ~~17~~ 10 wherein said seasoning film comprises silicon nitride.

13. (Currently amended) The method of claim ~~17~~ 10 wherein said seasoning film comprises silicon carbide.